NGTD20T120F2

IGBT Die

Trench Field Stop II IGBT Die for motor drive and inverter applications.

Features

- Extremely Efficient Trench with Field Stop Technology
- Low V_{CE(sat)} Loss Reduces System Power Dissipation

Typical Applications

- Industrial Motor Drives
- Solar Inverters
- UPS Systems
- Welding

MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Collector–Emitter Voltage, $T_J = 25^{\circ}C$	V _{CE}	1200	V
DC Collector Current, limited by $T_{J(\text{max})}$	Ι _C	(Note 1)	A
Pulsed Collector Current (Note 2)	I _{C, pulse}	100	А
Gate-Emitter Voltage	V _{GE}	±20	V
Maximum Junction Temperature	Τ _J	-55 to +175	°C
Short Circuit Withstand Time, V_{GE} = 15 V, V_{CE} = 500V, T_J \leq 150°C	T _{SC}	10	μs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Depending on thermal properties of assembly.

2. T_{pulse} limited by T_{jmax} , 10 µs pulse, V_{GE} = 15 V.

MECHANICAL DATA

Parameter	Value	Unit		
Die Size	5129 x 3695	μm ²		
Emitter Pad Size	See die layout	μm ²		
Gate Pad Size	400 x 670	μm ²		
Die Thickness	5	mils		
Wafer Size	150	mm		
Top Metal	5 μm AlSi			
Back Metal	2 μm TiNiAg			
Max possible chips per wafer	766			
Passivation frontside	Oxide-Nitride			
Reject ink dot size	25 mils			
Recommended storage environment: In original container, in dry nitrogen, or temperature of 18–28°C, 30–65%RH	Type: Bare Wafer in Jar Storage time: < 36 months	Type: Die on tape in ring–pack Storage time: < 3 months		

ORDERING INFORMATION

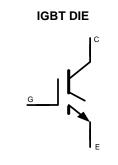
Device	Inking?	Shipping
NGTD20T120F2WP	Yes	Bare Wafer in Jar
NGTD20T120F2SWK	Yes	Sawn Wafer on Tape



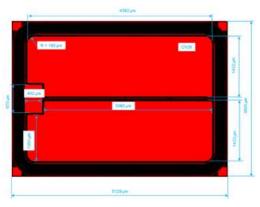
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V_{RCE} = 1200 V I_C = Limited by T_{J(max)}



DIE OUTLINE



NGTD20T120F2

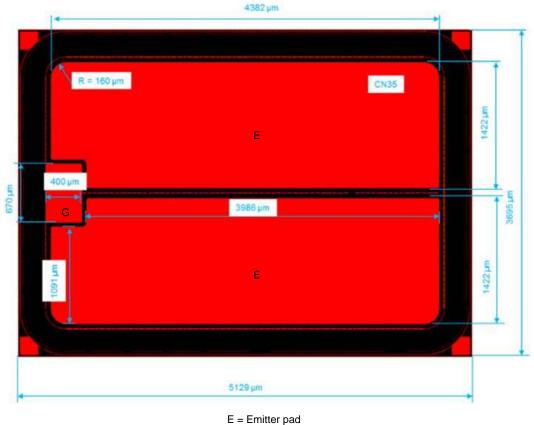
ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}C$, unless otherwise specified)

Parameter	Test Conditions	Symbol	Min	Тур	Max	Units
STATIC CHARACTERISTICS			•		•	•
Collector-Emitter Breakdown Voltage	V_{GE} = 0 V, I _C = 500 μ A	V _{(BR)CES}	1200			V
Collector-Emitter Saturation Voltage	V_{GE} = 15 V, I _C = 20 A	V _{CE(sat)}		2.0	2.4	V
Gate-Emitter Threshold Voltage	$V_{GE} = V_{CE}, I_C = 400 \ \mu A$	V _{GE(TH)}	4.5	5.5	6.5	V
Collector-Emitter Cutoff Current	V _{GE} = 0 V, V _{CE} = 1200 V	I _{CES}			0.4	mA
Gate Leakage Current	V_{GE} = 20 V, V_{CE} = 0 V	I _{GES}			200	nA
DYNAMIC CHARACTERISTICS						
Input Capacitance		Cian		4420		рF

Input Capacitance		Cies	4420	pF	
Output Capacitance	V _{CE} = 20 V, V _{GE} = 0 V, f = 1 MHz	C _{oes}	151	pF	
Reverse Transfer Capacitance		Cres	81	pF	ĺ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

DIE LAYOUT



E = Emitter pad G = Gate pad All dimensions in μm

Further Electrical Characteristic

Switching characteristics and thermal properties are depending strongly on module design and mounting technology and can therefore not be specified for a bare die.

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